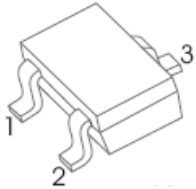


<b>TRANSISTOR(PNP)</b>	<b>SOT-323 Plastic-Encapsulate Transistors</b>
<p><b>SOT-323</b></p>  <p>1. BASE 2. EMITTER 3. COLLECTOR</p> <p>Marking :K4M</p>	<p><b>Features</b></p> <ul style="list-style-type: none"> <li>● Complementary to MMST5551</li> <li>● Small Surface Mount Package</li> <li>● Ideal for Medium Power Amplification and Switching</li> </ul>

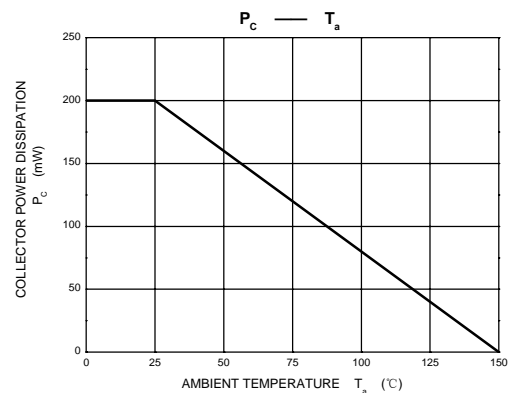
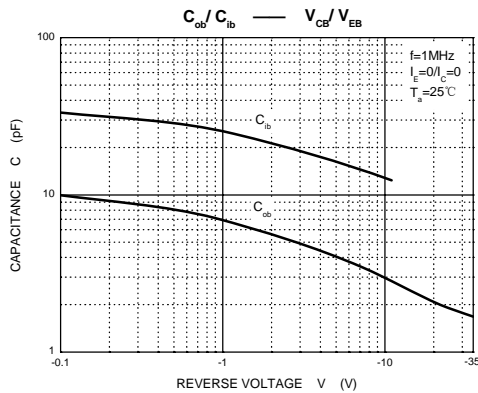
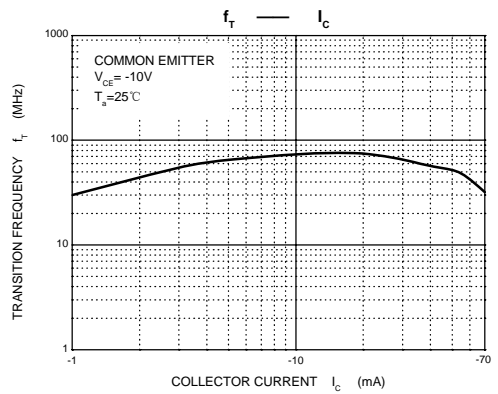
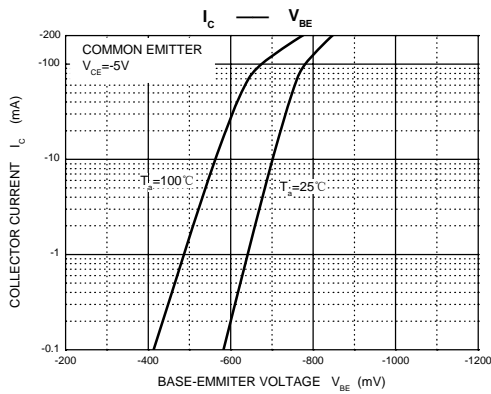
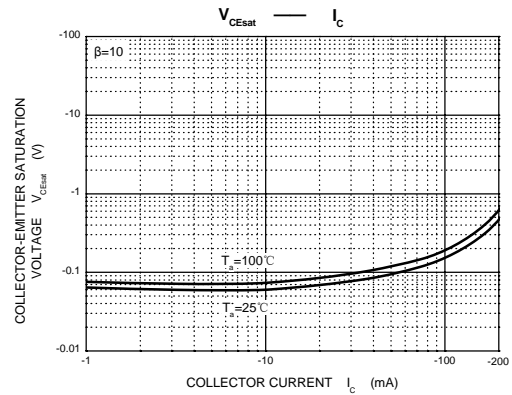
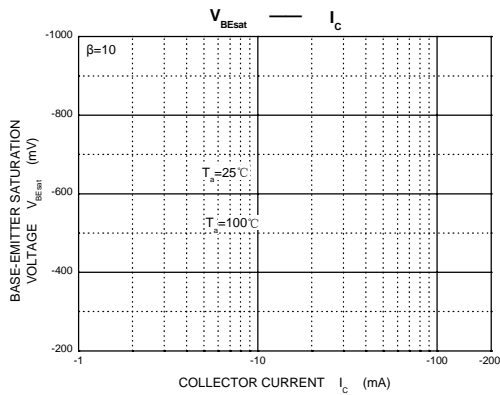
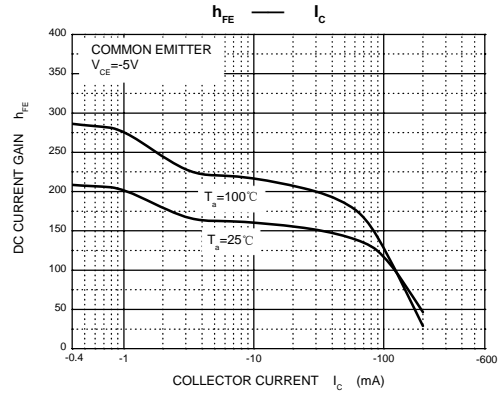
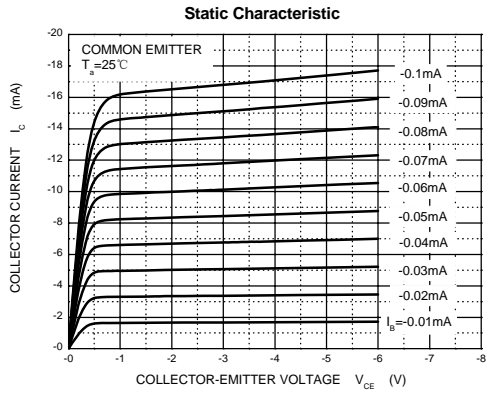
**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-150	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-600	mA
P <sub>C</sub>	Collector Power Dissipation	200	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

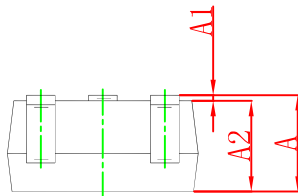
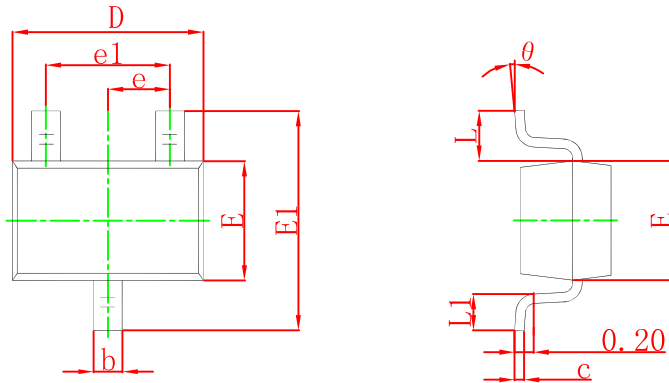
**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-160			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-150			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-120V, I <sub>E</sub> =0			-50	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-3V, I <sub>C</sub> =0			-50	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA	50			
		V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA	100		300	
		V <sub>CE</sub> =-5V, I <sub>C</sub> =-50mA	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-0.5	V
		I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA			-0.2	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-1	V
		I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA, f=100MHz	100			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz			6	pF

**Typical Characteristics**

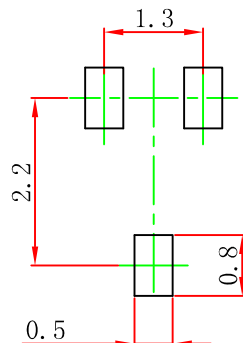


**SOT-323 Package Outline Dimensions**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

**SOT-323 Suggested Pad Layout**



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance:  $\pm 0.05$ mm.  
 3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)